

900V N-ch Planar MOSFET

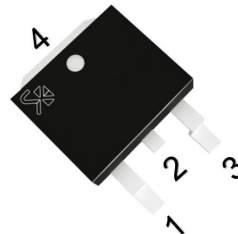
General Features

- RoHS Compliant
- $R_{DS(ON),typ.}=1.4\ \Omega @ V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

Applications

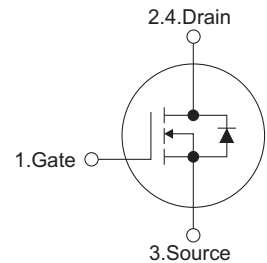
- Adaptor
- Charger
- SMPS Standby Power

BV_{DSS}	$R_{DS(ON),typ.}$	I_D
900V	1.4 Ω	6.0A



TO-263

Package No to Scale



Absolute Maximum Ratings

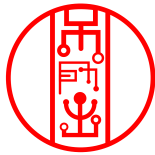
$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	SK06N90B-ST	Unit
V_{DSS}	Drain-to-Source Voltage	900	V
V_{GSS}	Gate-to-Source Voltage	± 30	
I_D	Continuous Drain Current	6.0	A
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$	24	
E_{AS}	Single Pulse Avalanche Energy	700	mJ
P_D	Power Dissipation	45	W
	Derating Factor above 25°C	0.29	W/ $^{\circ}\text{C}$
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	$^{\circ}\text{C}$
$T_J \& T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	SK06N90B-ST	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.78	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	



Electrical Characteristics

OFF Characteristics

 $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	900	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=900V, V_{GS}=0V$
		--	--	100		$V_{DS}=720V, V_{GS}=0V, T_J=125^{\circ}\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+30V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-30V, V_{DS}=0V$

ON Characteristics

 $T_J = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	1.4	1.9	Ω	$V_{GS}=10V, I_D=3A$
$V_{GS(TH)}$	Gate Threshold Voltage	3.0	--	5.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
gfs	Forward Transconductance	--	8.0	--	S	$V_{DS}=15V, I_D=3A$

Dynamic Characteristics

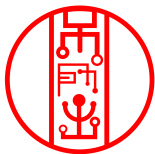
Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	1460	--	pF	$V_{GS}=0V, V_{DS}=25V, f=1.0\text{MHz}$
C_{rss}	Reverse Transfer Capacitance	--	23	--		
C_{oss}	Output Capacitance	--	130	--		
Q_g	Total Gate Charge	--	37	--	nC	$V_{DD}=450V, I_D=6A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	8.0	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	14	--		

Resistive Switching Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	22	--	nS	$V_{DD}=450V, I_D=6A, V_{GS}=10V, R_g=9.1\Omega$
t_{rise}	Rise Time	--	45	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	33	--		
t_{fall}	Fall Time	--	37	--		



Source-Drain Body Diode Characteristics

$T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[2]	--	--	6	A	Integral pn-diode in MOSFET
I_{SM}	Pulsed Source Current ^[2]	--	--	24		
V_{SD}	Diode Forward Voltage	--	--	1.5	V	$I_S=6\text{A}$, $V_{GS}=0\text{V}$
t_{rr}	Reverse Recovery Time	--	390	--	ns	$V_{GS}=0\text{V}$ $I_F=I_S$, $di/dt=100\text{A}/\mu\text{s}$
Q_{rr}	Reverse Recovery Charge	--	1.4	--	μC	



Typical Characteristics

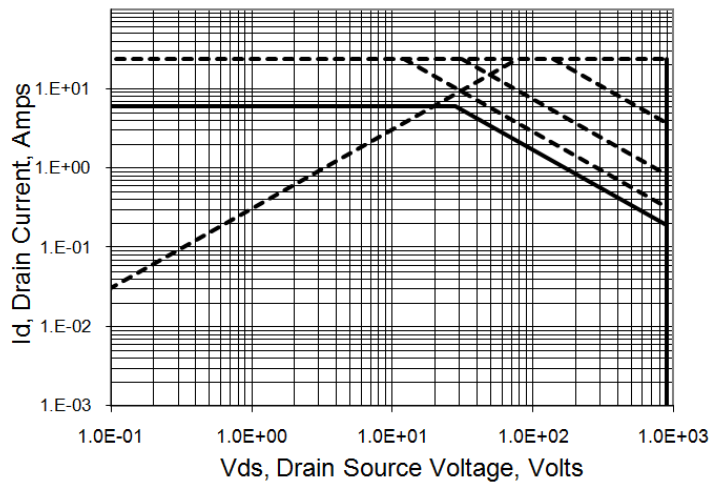


Figure 1 . Maximum Safe Operating Area

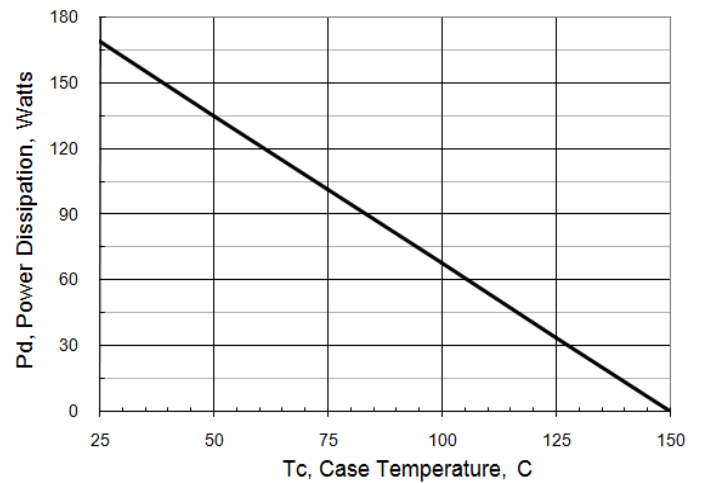


Figure 2 . Maximum Power Dissipation vs Case Temperature

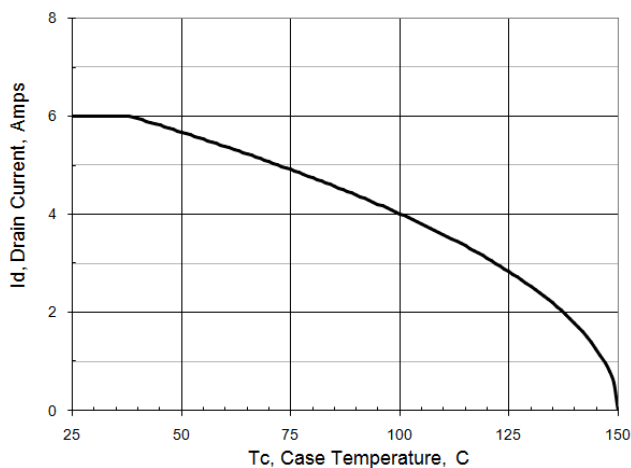


Figure 3 .Maximum Continuous Drain Current vs Case Temperature

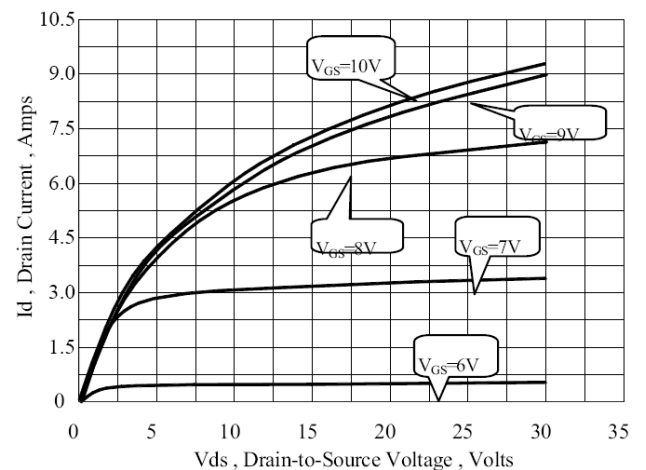


Figure 4 Typical Output Characteristics

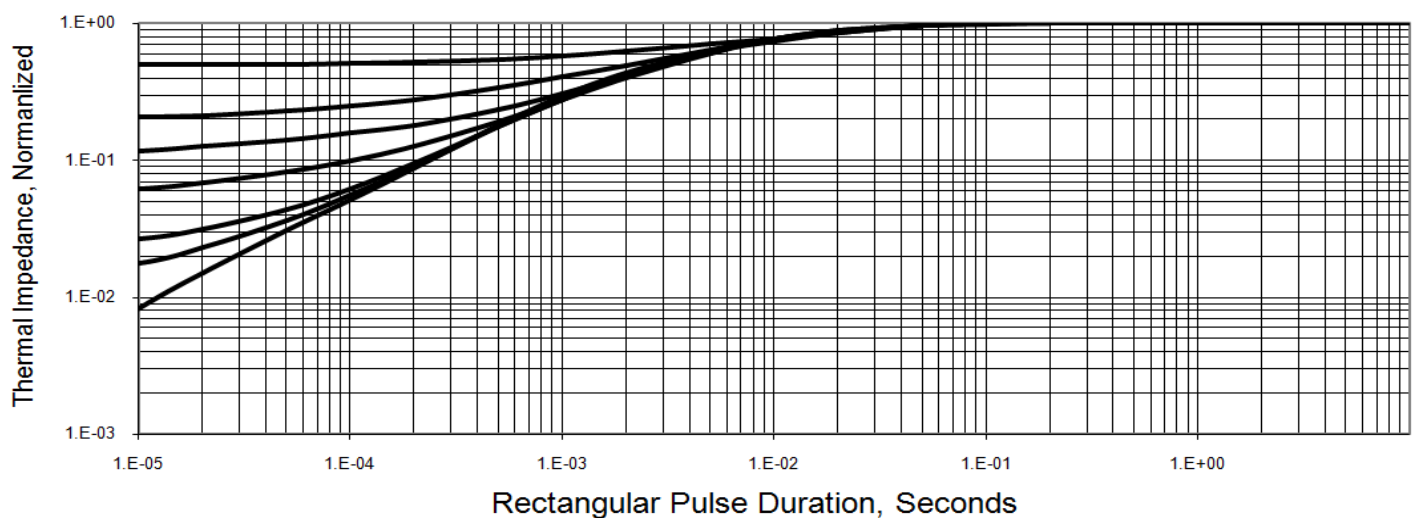
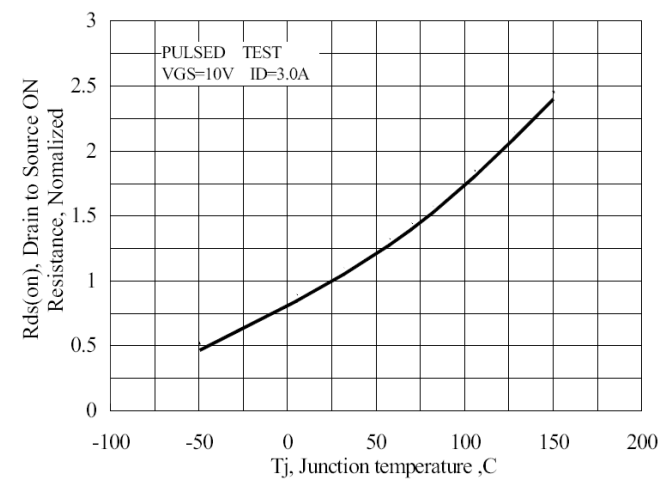
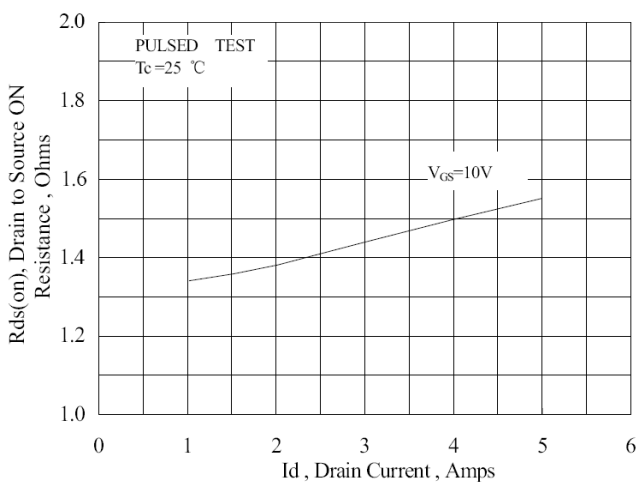
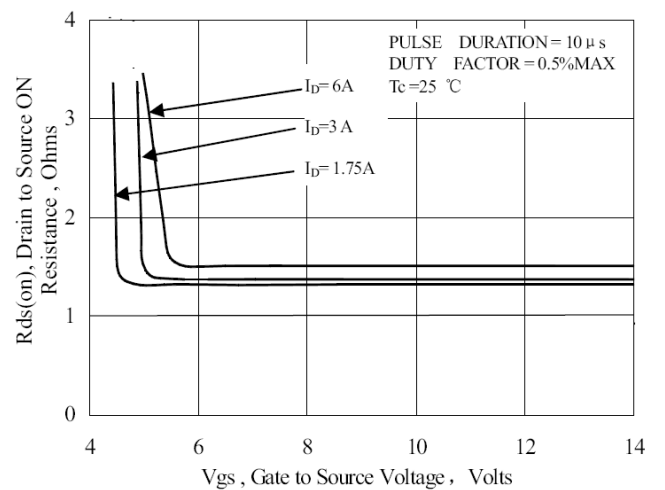
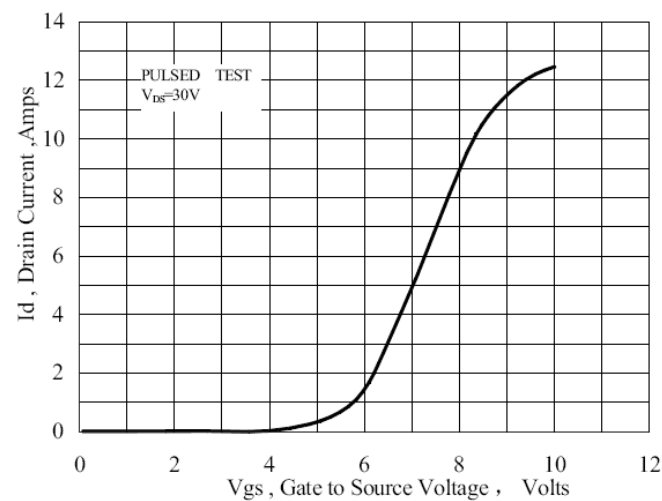
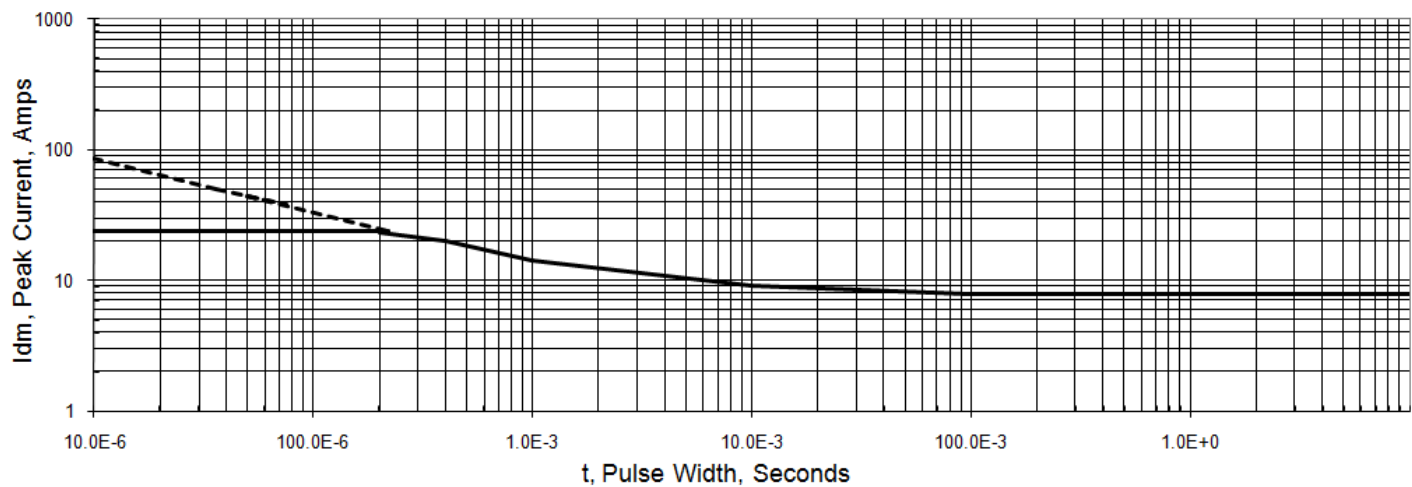
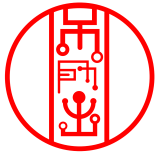


Figure 5. Maximum Transient Thermal Impedance



Typical Characteristics(Cont.)





Typical Characteristics(Cont.)

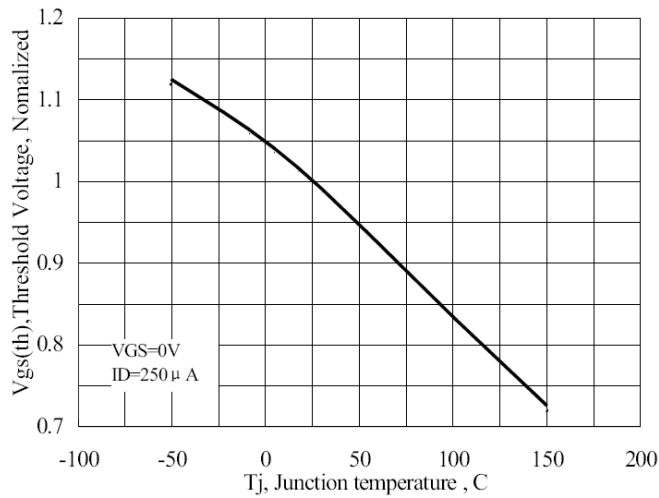


Figure 11 Typical Threshold Voltage vs Junction Temperature

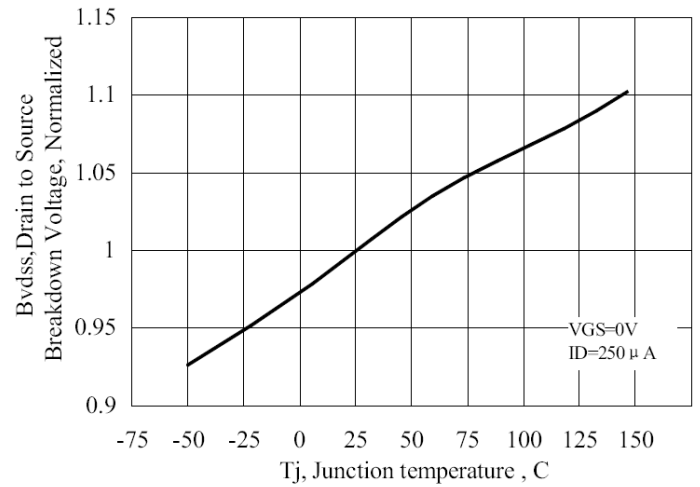


Figure 12 Typical Breakdown Voltage vs Junction Temperature

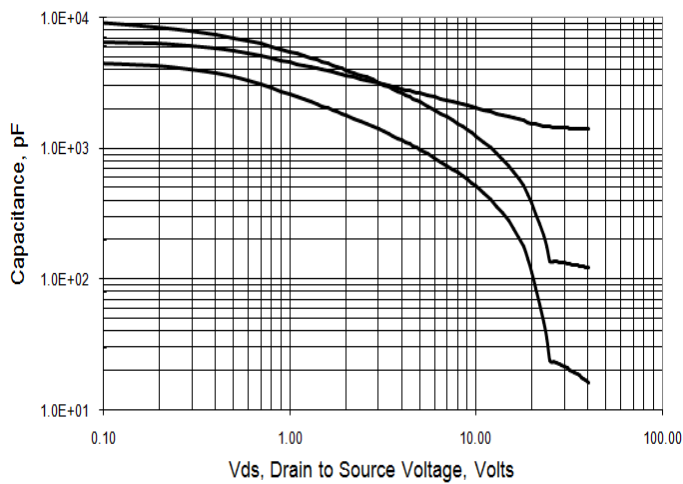


Figure 13. Capacitance vs Vds

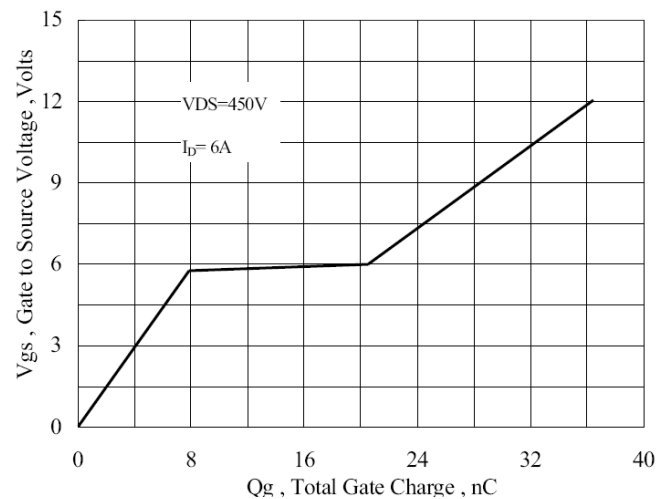


Figure 14 Typical Gate Charge vs Gate to Source Voltage

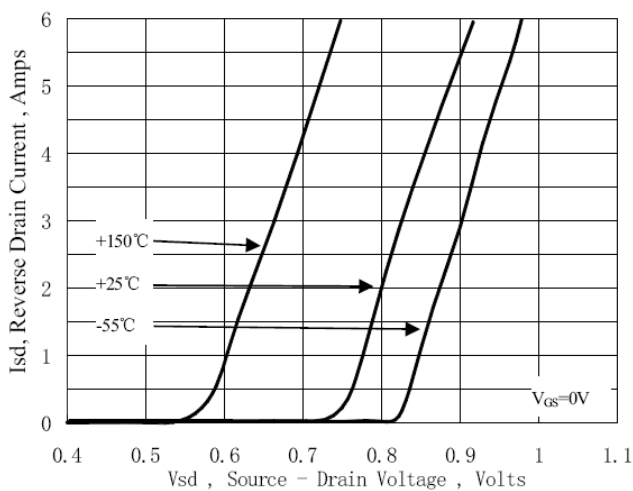


Figure 15 Typical Body Diode Transfer Characteristics

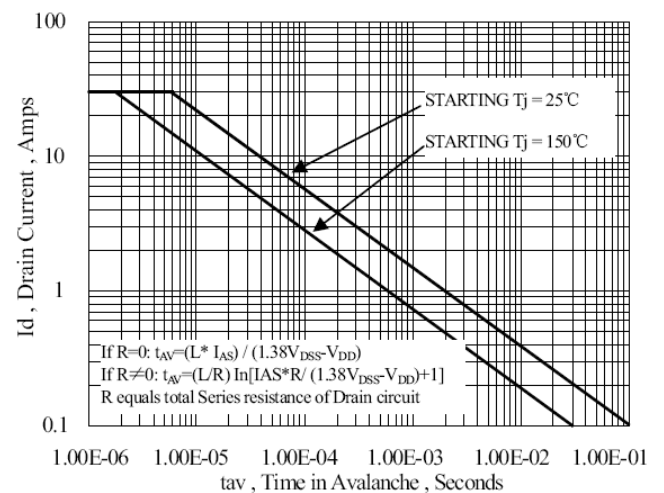


Figure 16 Unclamped Inductive Switching Capability

Test Circuits and Waveforms

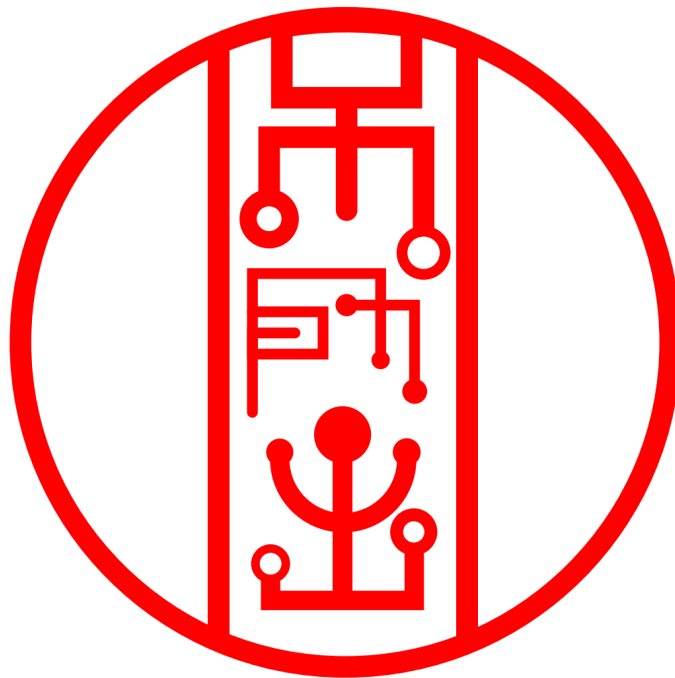


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

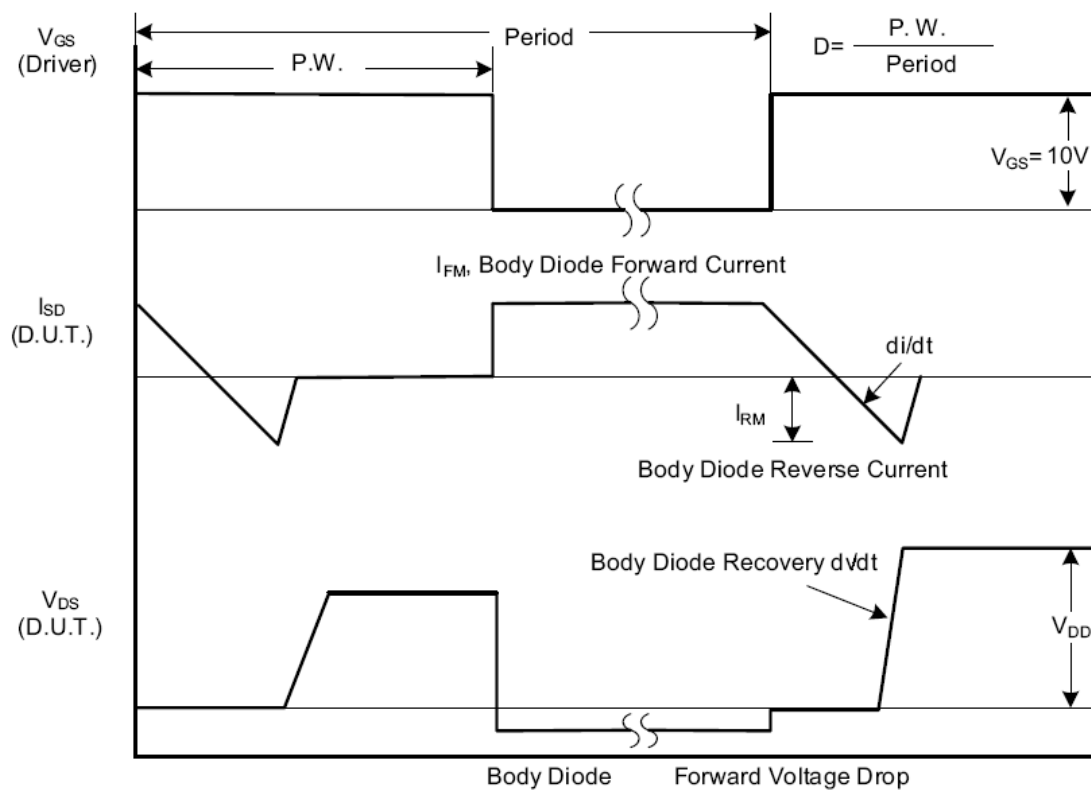


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

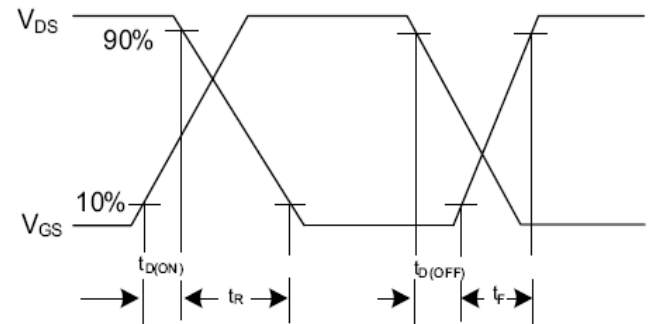
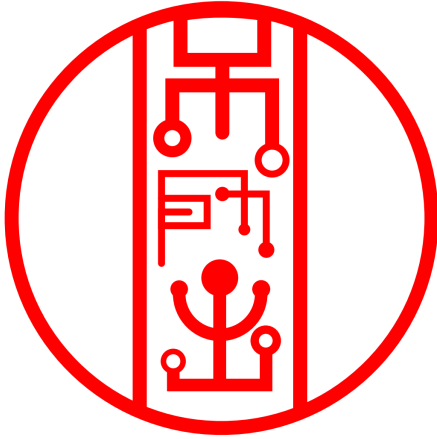


Fig. 2.2 Switching Waveforms

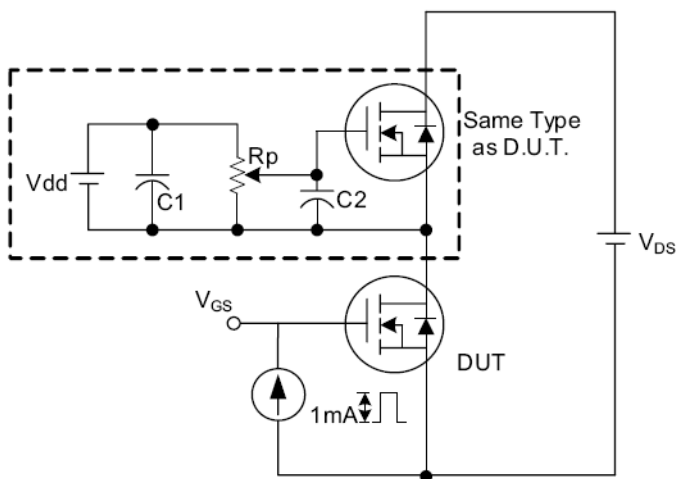


Fig. 3.1 Gate Charge Test Circuit

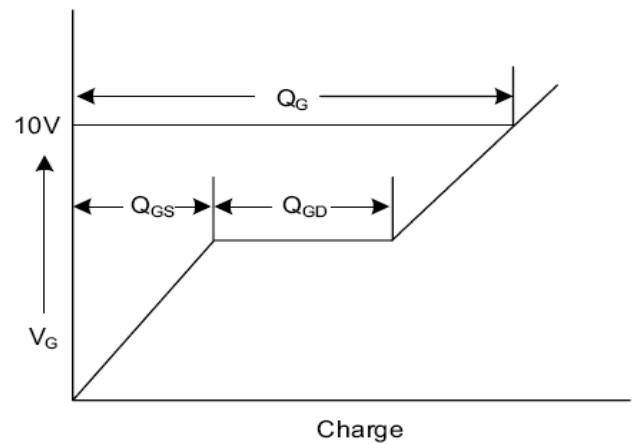


Fig. 3.2 Gate Charge Waveform

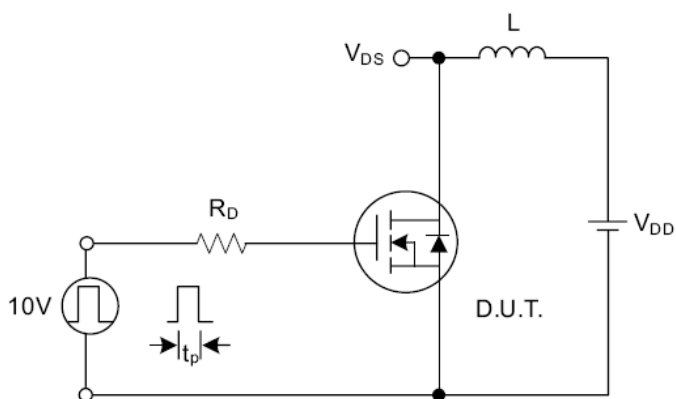


Fig. 4.1 Unclamped Inductive Switching Test Circuit

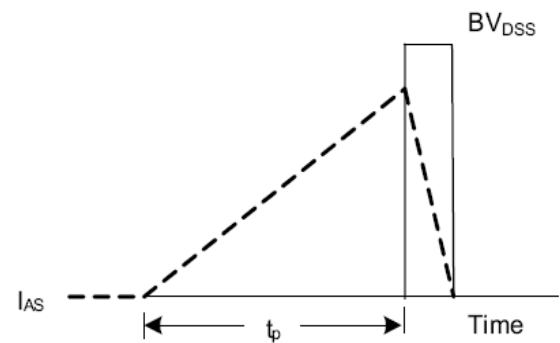
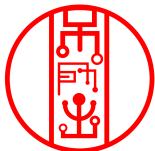


Fig. 4.2 Unclamped Inductive Switching Waveforms



SK06N90B-ST

PACKAGE OUTLINE

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